

WHAT IS CLAIMED IS:

1. A dummy wafer formed by sintering a mixture containing a silicon carbide powder and a non-metallic sintering auxiliary,
5 wherein

a coating film layer containing silicon carbide is provided on the surface of the dummy wafer including at least one of either upper and lower main faces of the dummy wafer by the chemical vapor deposition method.

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2. The dummy wafer according to claim 1, wherein the coating film layer containing silicon carbide is provided on the whole perimeter of the surface of the dummy wafer including the side surface of the dummy wafer.

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3. The dummy wafer according to claim 1 or 2, wherein the coating film layer has a thickness of 20 μm or more and 70 μm or less, and a surface roughness (Ra) of 10 nm or less.

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4. A method for manufacturing a dummy wafer formed by sintering a mixture containing a silicon carbide powder and a non-metallic sintering auxiliary, wherein

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the method for manufacturing a dummy wafer has a step of providing a coating film layer containing silicon carbide with a coating film thickness of 20 μm or more and 70 μm or less on the surface of the dummy wafer including at least one of either upper and lower main faces of the dummy wafer by the chemical

vapor deposition method.

5. The method for manufacturing a dummy wafer according to claim 4, wherein the coating film thickness of the coating
5 film layer is 20 μm or more and 40 μm or less.

6. The method for manufacturing a dummy wafer according to claim 4 or 5, further having a step of polishing the surface of the coating film layer.

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7. The method for manufacturing a dummy wafer according to claim 6, wherein the coating film layer after polishing the surface has a thickness of 20 μm or more and 70 μm or less, and a surface roughness (Ra) of 10 nm or less.

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8. The dummy wafer according to any one of claims 1 to 3, wherein the dummy wafer is for a monitor wafer.